# **Darlington Amplifier Transistors**

# **NPN Silicon**

## **Features**

 These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CES</sub>	30	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	30	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	10	Vdc
Collector Current - Continuous	I <sub>C</sub>	300	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

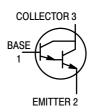
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



# ON Semiconductor®

http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 6

#### MARKING DIAGRAM



1x = Device Code

x = M for MMBTA13LT1

x = N for MMBTA14LT1

M = Date Code\*

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBTA13LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA14LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	·	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			I		<u> </u>
Collector – Emitter Breakdown Voltage ( $I_C = 100 \mu Adc, V_{BE} = 0$ )		V <sub>(BR)CES</sub>	30	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)		I <sub>CBO</sub>	_	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 10 \text{ Vdc}, I_C = 0$ )		I <sub>EBO</sub>	_	100	nAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ( $I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$ )	MMBTA13 MMBTA14	h <sub>FE</sub>	5000 10,000	- -	_
$(I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBTA13 MMBTA14		10,000 20,000	-	
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0.1 mAdc)		V <sub>CE(sat)</sub>	-	1.5	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5.0 Vdc)		V <sub>BE</sub>	_	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)		f <sub>T</sub>	125	-	MHz

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%. 4.  $f_T = |h_{fe}| \bullet f_{test}$ .

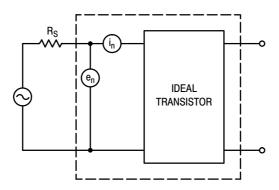


Figure 1. Transistor Noise Model

## **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

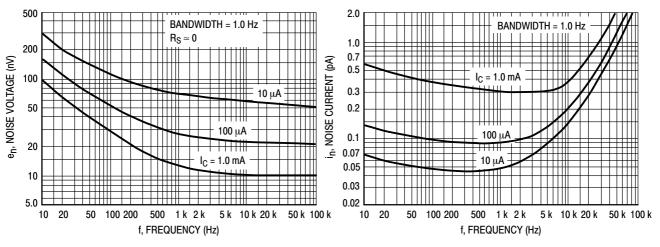


Figure 2. Noise Voltage

Figure 3. Noise Current

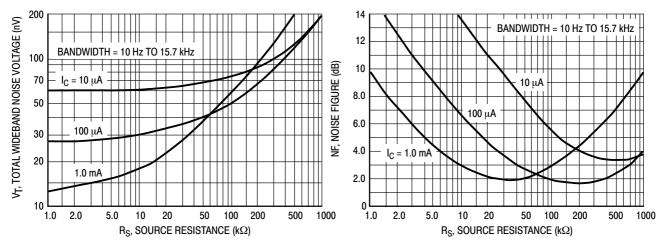


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

#### SMALL-SIGNAL CHARACTERISTICS

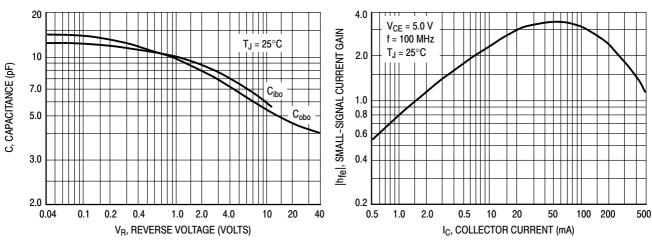


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

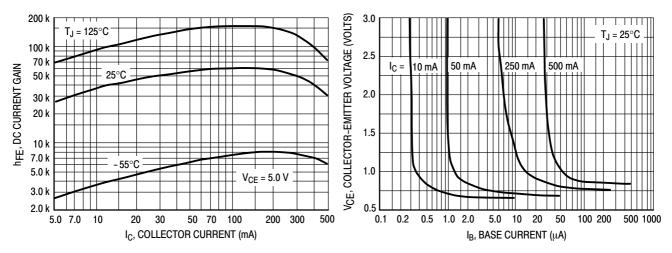


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

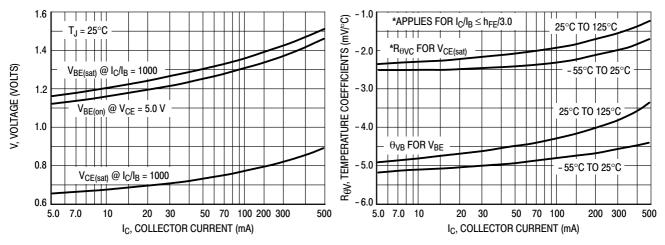


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

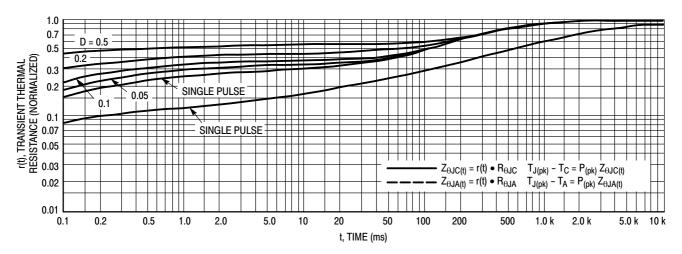


Figure 12. Thermal Response

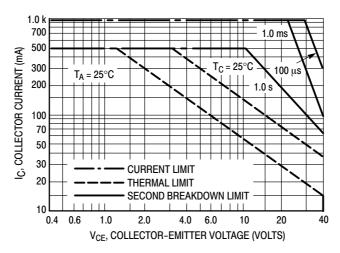
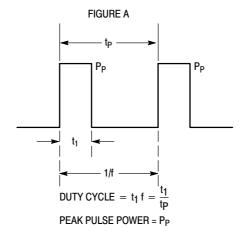


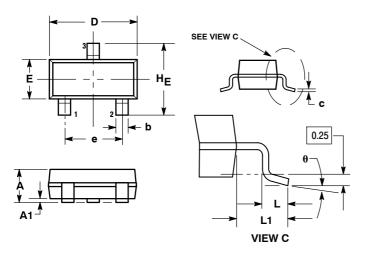
Figure 13. Active Region Safe Operating Area



**Design Note: Use of Transient Thermal Resistance Data** 

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

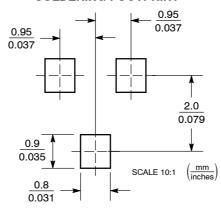
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

### STYLE 6:

PIN 1. BASE

- EMITTER 2. 3.
- COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and war engineer trademarks of semiconductor components industries, Ite (SciLLC) solitate services are injective to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA **Phone**: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Cer Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative